Diode Semiconductor Device - Page 1 of 1



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| Inclosure N | laterial: |
|---------------|--|
| Glass and m | netal |
| Overall Len | igth: |
| 1.000 inches | ŝ |
| Terminal Le | ength: |
| 1.000 inches | S |
| Overall Dia | meter: |
| 0.375 inches | 3 |
| Mounting N | lethod: |
| Terminal | |
| Features Pr | rovided: |
| Hermetically | / sealed case |
| Semicondu | ictor Material: |
| Silicon | |
| Voltage Rat | ting In Volts Per Characteristic: |
| 5000.0 reve | erse voltage, peak |
| Current Rat | ting Per Characteristic: |
| 200.00 millia | amperes forward current, average absolute |
| Maximum C | Operating Tempurature Per Measurement Point: |
| 150.0 degre | es celsius ambient air |
| Terminal Ty | ype And Quantity: |
| 2 uninsulate | d wire lead |
| Shelf Life: | |
| N/a | |
| Unit Of Mea | asure: |
| | |
| Demilitariza | ation: |
| No | |
| Fiig: | |
| A110a0 | |